

**SDR3ASMS
 thru
 SDR3NSMS**

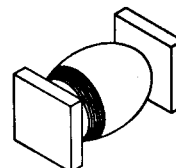
Designer's Data Sheet

FEATURES:

- Ultra Fast Recovery: 50-80 nsec Max. @ 25°C
 85-125 nsec Max. @ 100°C
- Single Chip Construction
- PIV to 1200 Volts
- Low Reverse Leakage Current
- Hermetically Sealed Surface Mount package
- For High Efficiency Applications
- Metallurgically Bonded
- Available in axial leaded versions
- TX, TXV and Space Level Screening Available

**3 AMP
 50-1200 VOLTS
 50-80 nsec
 ULTRA FAST
 RECTIFIER**

**SURFACE MOUNT
 SQUARE TAB**



MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse and DC Blocking Voltage	SDR3ASMS SDR3BSMS SDR3DSMS SDR3GSMS SDR3JSMS SDR3KSMS SDR3MSMS SDR3NSMS	VRRM VRWM VR	Volts
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, TA=25°C)	IO	3	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on IO, allow junction to reach equilibrium between pulses, TA=25°C)	IFSM	75	Amps
Operating and storage temperature	Top & Tstg	-65 to +175	°C
Maximum Thermal Resistance Junction to End Tab	RθJE	14	°C/W

NOTE: All specifications are subject to change without notification.
 SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: RU0091 A

RMD

SDR3ASMS thru SDR3NSMS

PRELIMINARY



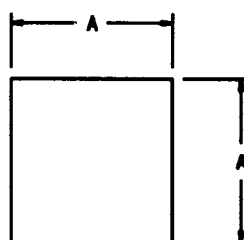
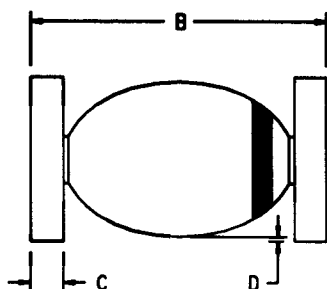
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ELECTRICAL CHARACTERISTICS

CHARACTERISTICS		SYMBOL	MAXIMUM	UNIT
Instantaneous Forward Voltage Drop ($I_F = 3 \text{ A}$, $T_A = 25^\circ\text{C}$, 300 μs Pulse)	SDR3ASMS-3JSMS SDR3KSMS-3NSMS	V_F	1.7 1.9	Vdc
Instantaneous Forward Voltage Drop ($I_F = 3 \text{ A}$, $T_A = -55^\circ\text{C}$, 300 μs Pulse)	SDR3ASMS-3JSMS SDR3KSMS-3NSMS	V_F	1.9 2.1	Vdc
Reverse Leakage Current (Rated V_R , $T_A = 25^\circ\text{C}$, 300 μs pulse minimum)		I_R	5	μA
Reverse Leakage Current (Rated V_R , $T_A = 100^\circ\text{C}$, 300 μs pulse minimum)		I_R	0.5	mA
Junction Capacitance ($V_R = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$)		C_J	40	pf
Reverse Recovery Time ($I_F = 500 \text{ mA}$, $I_R = 1 \text{ A}$, $I_{RR} = 250 \text{ mA}$, $T_A = 25^\circ\text{C}$)	SDR3ASMS-3JSMS SDR3KSMS SDR3MSMS-3NSMS	t_{rr}	50 60 70 80	nsec

CASE OUTLINE:



Dimensions prior to solder dipping.

DIMENSIONS

DIM	MIN.	MAX.
A	.172"	.180"
B	.180"	.280"
C	.022"	.028"
D	.002"	---

TYPICAL OPERATING CURVES

$T_A = 25^\circ\text{C}$ Unless otherwise specified

